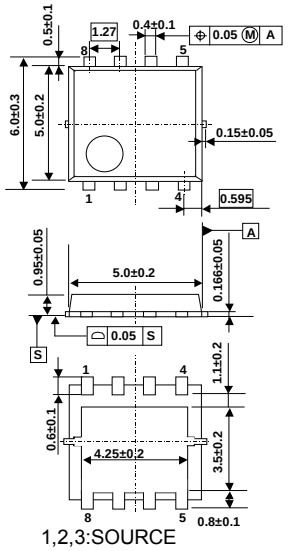
TOSHIBA Field Effect Transistor Silicon P Channel MOS Type (U-MOSⅢ)

TPCA8102

Lithium Ion Battery Applications
Notebook PC Applications
Portable Equipment Applications

- Small footprint due to small and thin package
- Low drain-source ON resistance: $R_{DS\ (ON)}$ = 4.5mΩ (typ.)
- High forward transfer admittance: $|Y_{fs}|$ = 60S (typ.)
- Low leakage current: I_{DSS} = −10 μA (max) (V_{DS} = −30 V)
- Enhancement mode: V_{th} = −0.8 to −2.0 V (V_{DS} = −10 V, I_D = −1 mA)

Unit: mm



1,2,3:SOURCE
4:GATE
5,6,7,8:DRAIN

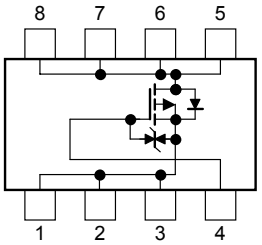
JEDEC	―
JEITA	―
TOSHIBA	2-5Q1A

Weight: 0.076 g (typ.)

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	−30	V
Drain-gate voltage (R_{GS} = 20 kΩ)		V_{DGR}	−30	V
Gate-source voltage		V_{GSS}	±20	V
Drain current	DC (Note 1)	I_D	− 40	A
	Pulsed (Note 1)	I_{DP}	−120	
Drain power dissipation (Tc=25°C)		P_D	45	W
Drain power dissipation (t = 10 s) (Note 2a)		P_D	2.8	W
Drain power dissipation (t = 10 s) (Note 2b)		P_D	1.6	W
Single pulse avalanche energy (Note 3)		E_{AS}	208	mJ
Avalanche current		I_{AR}	− 40	A
Repetitive avalanche energy (Tc=25°C) (Note 4)		E_{AR}	4.5	mJ
Channel temperature		T_{ch}	150	°C
Storage temperature range		T_{stg}	−55 to 150	°C

Circuit Configuration



Note: For Notes 1 to 4, refer to the next page.

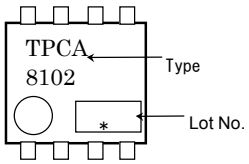
Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook (“Handling Precautions”/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device.
Please handle with caution.

Thermal Characteristics

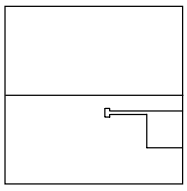
Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case (Tc=25°C)	$R_{th\ (ch\text{-}c)}$	2.78	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	$R_{th\ (ch\text{-}a)}$	44.6	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	$R_{th\ (ch\text{-}a)}$	78.1	°C/W

Marking (Note 5)



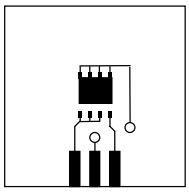
Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a) (b) Device mounted on a glass-epoxy board (b)



FR-4
25.4 × 25.4 × 0.8
(Unit: mm)

(a)



FR-4
25.4 × 25.4 × 0.8
(Unit: mm)

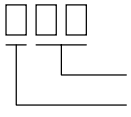
(b)

Note 3: V_{DD} = 24 V, T_{ch} = 25°C (initial), L = 100 μH, R_G = 25 Ω, I_{AR} = − 40 A

Note 4: Repetitive rating: pulse width limited by max channel temperature

Note 5: "○" on the lower left of the marking indicates Pin 1.

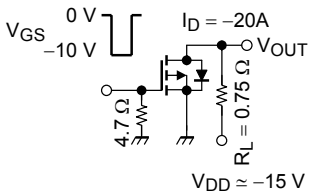
* Weekly code (three digits):



Week of manufacture
(01 for the first week of the year, continuing up to 52 or 53)

Year of manufacture
(Last digit of the calendar year)

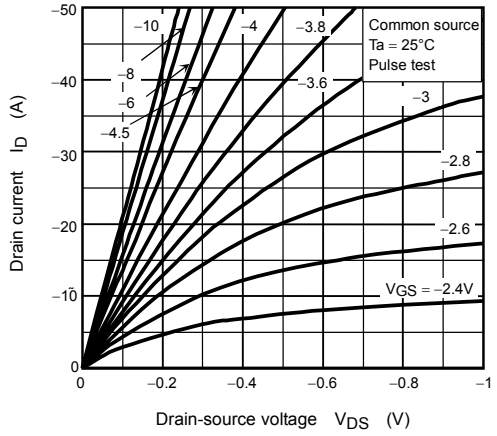
Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	V_{GS} = ±16 V, V_{DS} = 0 V	—	—	±10	μA
Drain cut-OFF current		I_{DSS}	V_{DS} = −30 V, V_{GS} = 0 V	—	—	−10	μA
Drain-source breakdown voltage		$V_{(BR)\ DSS}$	I_D = −10 mA, V_{GS} = 0 V	−30	—	—	V
		$V_{(BR)\ DSX}$	I_D = −10 mA, V_{GS} = 20 V	−15	—	—	
Gate threshold voltage		V_{th}	V_{DS} = −10 V, I_D = − 1 mA	−0.8	—	−2.0	V
Drain-source ON resistance		$R_{DS\ (ON)}$	V_{GS} = −4 V, I_D = −20 A	—	9.0	14	mΩ
			V_{GS} = −10 V, I_D = −20 A	—	4.5	6.0	
Forward transfer admittance		$\|Y_{fs}\|$	V_{DS} = −10 V, I_D = −20 A	30	60	—	S
Input capacitance		C_{iss}	V_{DS} = −10 V, V_{GS} = 0 V, f = 1 MHz	—	4600	—	pF
Reverse transfer capacitance		C_{rss}		—	850	—	
Output capacitance		C_{oss}		—	980	—	
Switching time	Rise time	t_r	 Duty ≦ 1%, t_w = 10 μs	—	10	—	ns
	Turn-ON time	t_{on}		—	20	—	
	Fall time	t_f		—	78	—	
	Turn-OFF time	t_{off}		—	220	—	
Total gate charge (gate-source plus gate-drain)		Q_g	V_{DD} ≃ −24 V, V_{GS} = 10 V, I_D = −40 A	—	109	—	nC
Gate-source charge 1		Q_{gs1}		—	24	—	
Gate-drain (“miller”) charge		Q_{gd}		—	25	—	

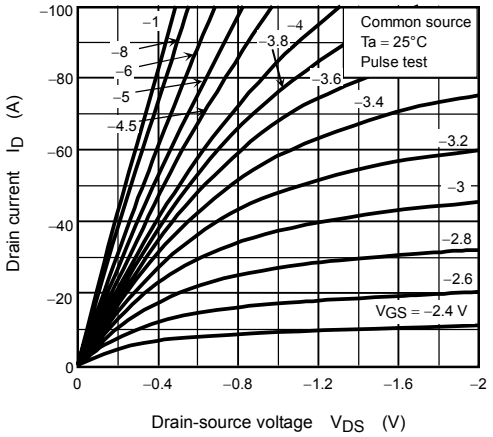
Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Drain reverse current	Pulse (Note 1)	I_{DRP}	—	—	—	−120	A
Forward voltage (diode)		V_{DSF}	I_{DR} = −40 A, V_{GS} = 0 V	—	—	1.2	V

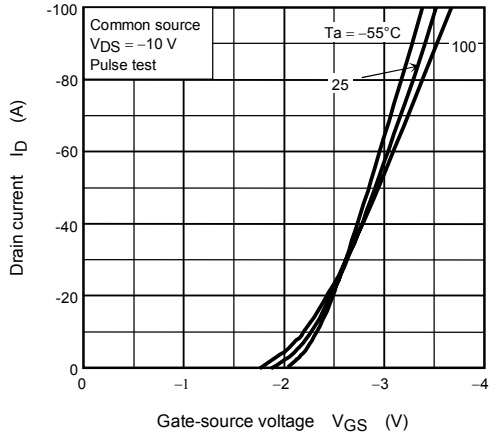
$I_D - V_{DS}$



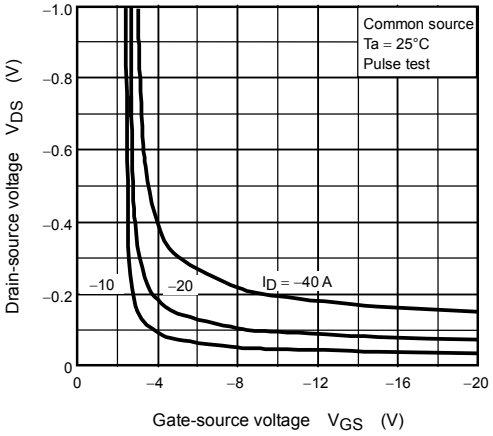
$I_D - V_{DS}$



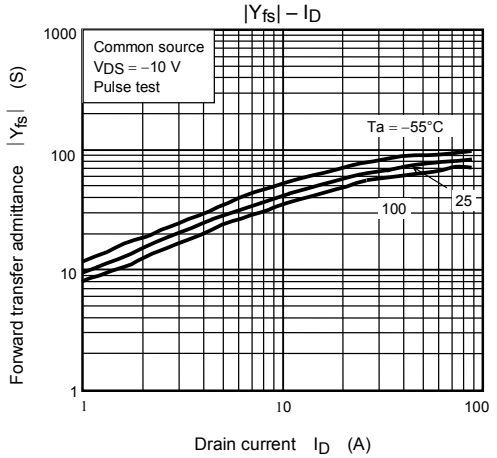
$I_D - V_{GS}$



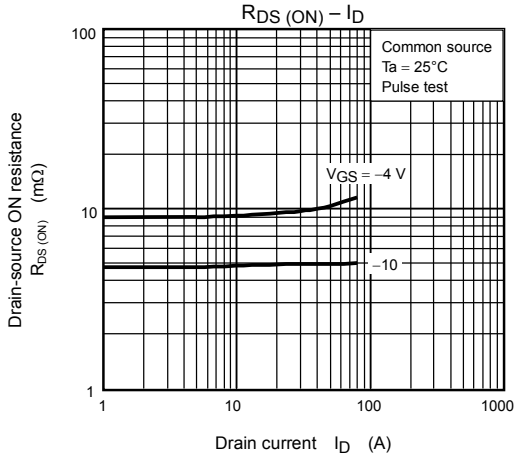
$V_{DS} - V_{GS}$



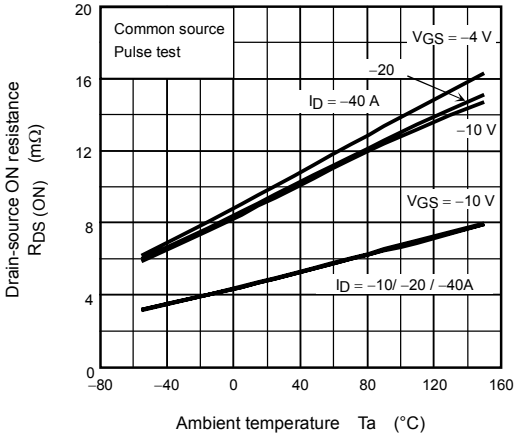
$|Y_{fs}| - I_D$



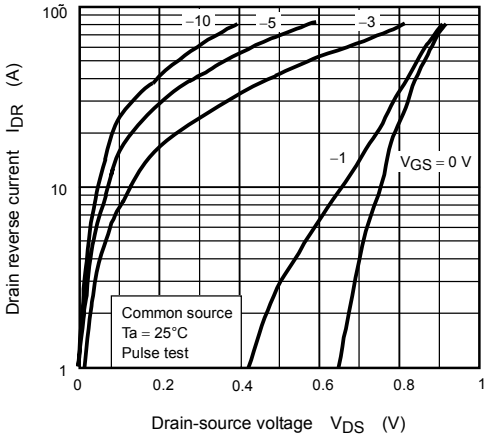
$R_{DS\ (ON)} - I_D$



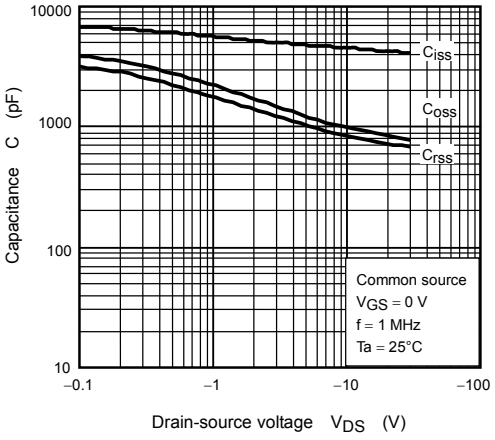
$R_{DS\ (ON)}$ – Ta



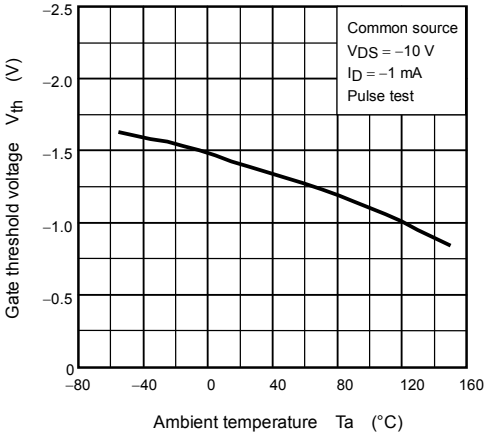
I_{DR} – V_{DS}



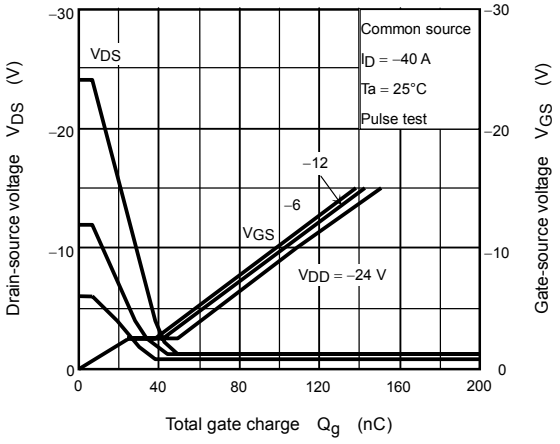
Capacitance – V_{DS}



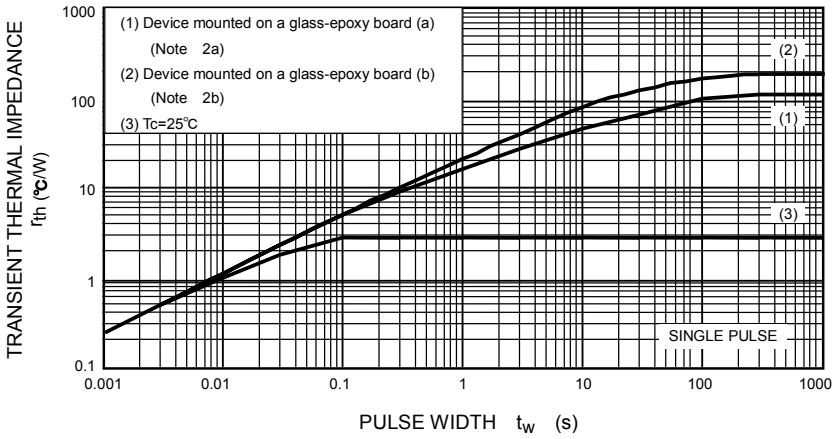
V_{th} – Ta



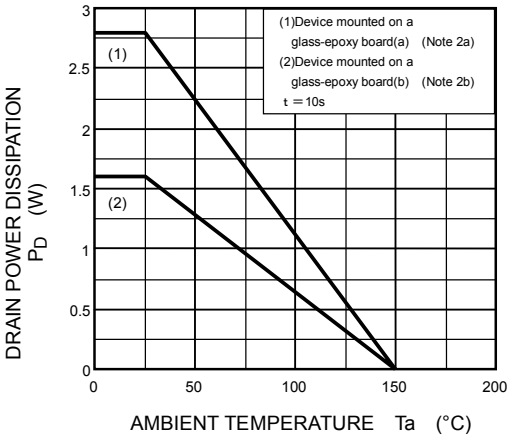
Dynamic input/output characteristics



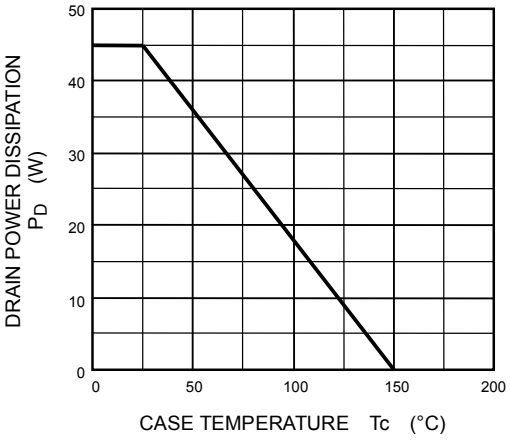
$r_{th} - t_w$



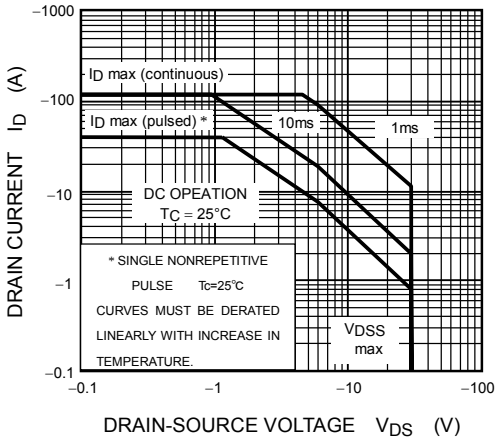
$P_D - Ta$



$P_D - Tc$



SAFE OPERATING AREA



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